

Substitute for form 1449A/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				Application Number	
				New Application	
				Filing Date	
				October 6, 2003	
				First Named Inventor	
		Shunpei YAMAZAKI et al.			
Art Unit		2824			
Examiner Name		M. Lebentritt			
Sheet	1	of	2	Attorney Docket Number	740756-2659

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
MSL		US-5,700,333	12/23/1997	Yamazaki et al.	
		US-4,561,171	12/31/1985	Schlosser	
		US-5,147,826	09/15/1992	Liu et al.	
		US-5,229,306	07/20/1993	Lindberg	
		US-5,244,819	09/14/1993	Yue	
		US-5,275,851	01/04/1994	Fonash et al.	
		US-5,441,899	08/15/1995	Nakai	
		US-5,444,001	08/22/1995	Tokuyama	
		US-5,529,937	06/25/1996	Zhang	
		US-5,696,011	12/09/1997	Nakata et al.	
		US-5,796,116	08/18/1998	Nakata et al.,	
		US-5,828,429	10/27/1998	Takemura	
		US-5,899,709	05/04/1999	Yamzaki et al.	
		US-6,048,758	04/11/2000	Yamazaki et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Country Code <sup>2</sup> Number <sup>3</sup> Kind Code <sup>3</sup> (if known)				
MSL		JP6333824	12/02/1994			Abstract
MSL		JP6333825	12/02/1994			Full & Abstract
MSL		JP 03-229415	10/11/1991			Abstract
MSL		JP 06-333824	12/02/1994			Abstract

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
MSL		DVURECHENSKII.A, TRANSPORT PHENOMENA IN AMORPHOUS SILICON DOPED BY ION IMPLANTATION OF 3D METALS, PP.635-640PHYS. STAT. SOL.	
MSL		HAYZELDEN.C, IN SITU TRANSMISSION ELECTRON MICROSCOPY STUDIES OF SILICIDE-MEDIATED CRYSTALLIZATION OF AMORPHOUS SILICON, VOL.60/PP.225-227APPL. PHYS. LETT.	
MSL		HEMPEL.T, NEEDLE-LIKE CRYSTALLIZATION OF NI DOPED AMORPHOUS SILICON THIN FILMS, VOL.85/PP.921-92450LID STATE COMMUNICATIONS	
MSL		KAKKAD.R, CRYSTALLIZED SI FILMS BY LOW-TEMPERATURE RAPID THERMAL ANNEALING OF AMORPHOUS SILICON, VOL. 65/PP. 2069-2072J. APPL. PHYS.	
MSL		KAKKAD.R, LOW TEMPERATURE SELECTIVE CRYSTALLIZATION OF AMORPHOUS SILICON, VOL. 11 51PP.66-68JOURNAL OF NON-CRYSTALLINE SOLIDS	

Examiner Signature	<i>M. Lebentritt</i>	Date Considered	12/20/04
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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				Filing Date	October 6, 2003
				First Named Inventor	Shunpei YAMAZAKI et al.
				Art Unit	2854
				Examiner Name	M. Lebentritt
Sheet	2	of	2	Attorney Docket Number	740756-2659

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PML		US-5,789,284	08/1998	Yamazaki et al.	
		US-6,331,457	12/2001	Yamazaki et al.	
		US-6,218,219	04/2001	Yamazaki et al.	
		US-6,197,624	03/2001	Yamazaki	
		US-6,048,758	04/2000	Yamazaki et al.	
		US-6,348,368	02/2002	Yamazaki et al.	
		US-2001/0041397	05/2001	Fukushima	
		US-2002/0013114	07/2001	Ohtani et al.	
		US-6,013,544	01/11/2000	Makita et al.	

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PML		LIU.G, SELECTIVE AREA CRYSTALLIZATION OF AMORPHOUS SILICON FILMS BY LOW-TEMPERATURE RAPID THERMAL ANNEALING, VOL.551PP.660-662APPL. PHYS. LETT.	
PML		LIU.G, "POLYCRYSTALLINE SILICON THIN FILM TRANSISTORS ON CORNING 7059 GLASS SUBSTRATES USING SHORT TIME, VOL. 62/PP.2554-2556APPL. PHYS. LETT.	

Examiner Signature	<i>M. Lebentritt</i>	Date Considered	12/20/04
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